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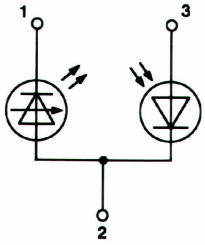
RLT85500G TECHNICAL DATA

High Power Infrared Laserdiode

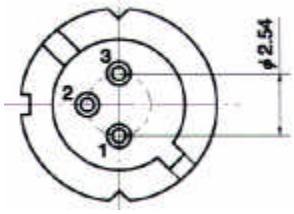
Aperture: **1.5 x 120 µm**
Lasing wavelength: **850 nm typ.**
Optical power: **500 mW typ.**
Package: **9 mm**

NOTE!
LASERDIODE
MUST BE COOLED!

PIN CONNECTION:



1) Laser diode cathode
2) Laser diode anode and photodiode cathode
3) Photodiode anode



Absolute Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	550	mW
LD Reverse Voltage	$V_{R(LD)}$	0.5	V
PD Reverse Voltage	$V_{R(PD)}$	25	V
Operation Case Temperature	T_C	-20 .. +40	°C
Storage Temperature	T_{STG}	-60 .. +60	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P_o	kink free		500		mW
Threshold Current	I_{th}	cw		230	260	mA
Operation Current	I_{op}	P_o = 500 mW	800	900	1100	mA
Operating Voltage	V_{op}	P_o = 500 mW		1.8	2.2	V
Lasing Wavelength	λ_p	P_o = 500 mW	800	850	870	nm
Spectral Width	$\Delta\lambda$	P_o = 500 mW		2	3	nm
Beam Divergence	$\theta_{//}$	P_o = 500 mW	8	12	20	°
Beam Divergence	$\theta_{\perp}$	P_o = 500 mW	20	30	40	°
Monitor Current	I_m	P_o = 500 mW	200		5000	µA